

# 2SK1636(L), 2SK1636(S)

Silicon N-Channel MOS FET

**HITACHI**

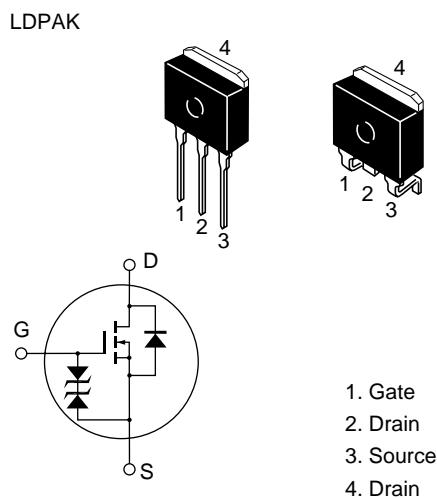
## Application

High speed power switching

## Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

## Outline



## **2SK1636(L), 2SK1636(S)**

### **Absolute Maximum Ratings (Ta = 25°C)**

<b>Item</b>	<b>Symbol</b>	<b>Ratings</b>	<b>Unit</b>
Drain to source voltage	V <sub>DSS</sub>	250	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	15	A
Drain peak current	I <sub>D(pulse)</sub> <sup>*1</sup>	60	A
Body to drain diode reverse drain current	I <sub>DR</sub>	15	A
Channel dissipation	Pch <sup>*2</sup>	75	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes 1. PW ≤ 10 μs, duty cycle ≤ 1%

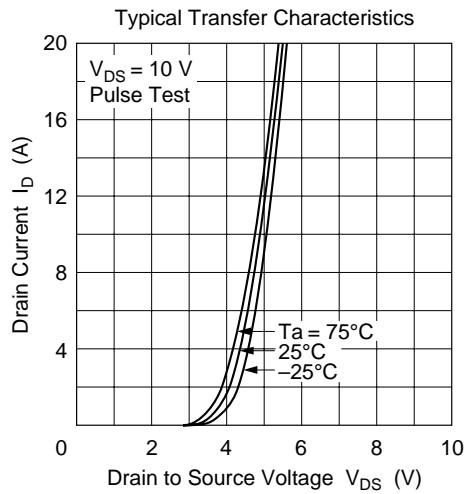
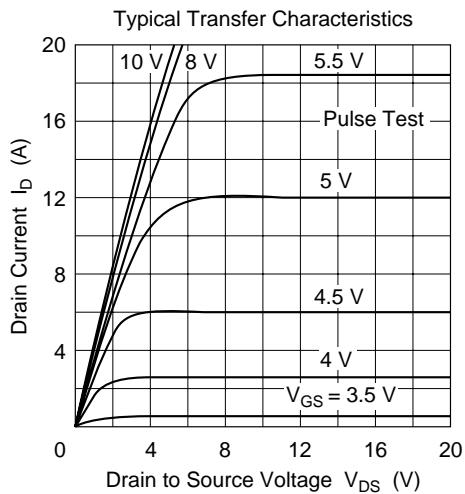
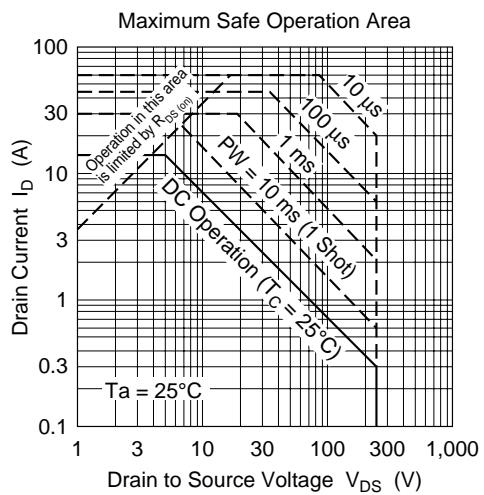
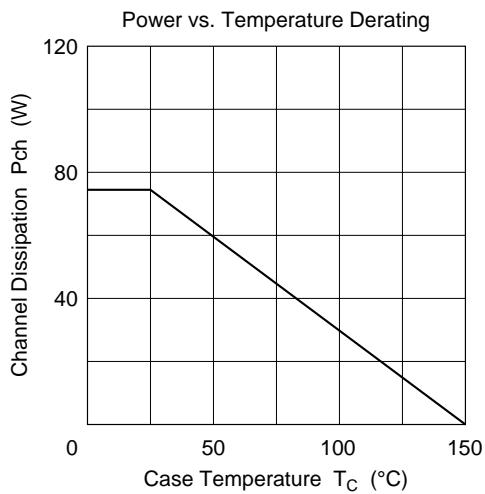
2. Value at T<sub>c</sub> = 25°C

**Electrical Characteristics (Ta = 25°C)**

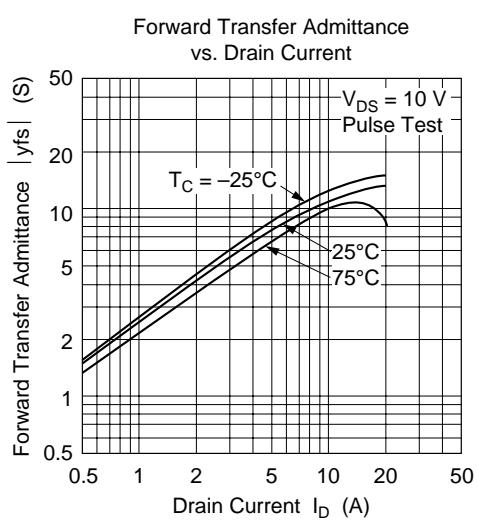
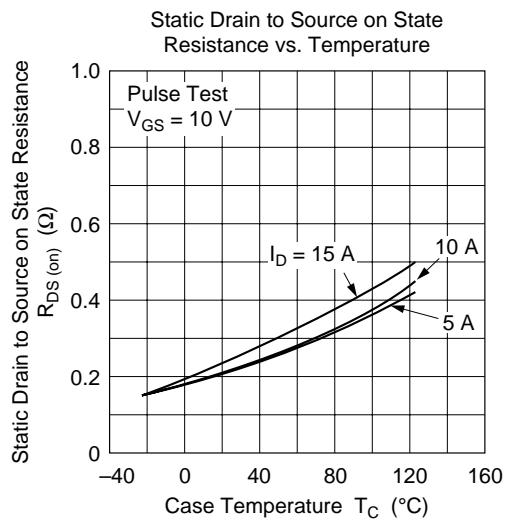
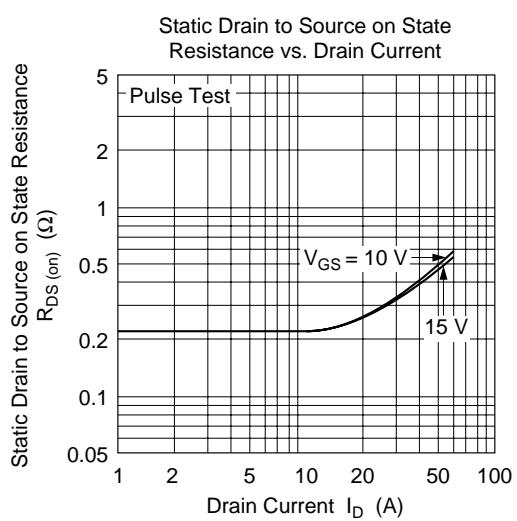
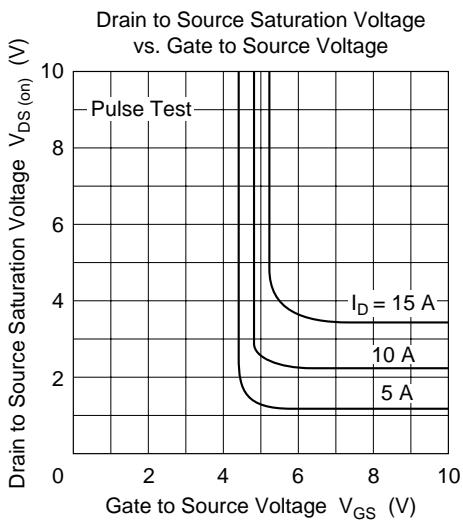
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	250	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±30	—	—	V	I <sub>G</sub> = ±100 µA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	250	µA	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.0	—	3.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static Drain to source on state resistance	R <sub>DS(on)</sub>	—	0.22	0.27	Ω	I <sub>D</sub> = 8 A, V <sub>GS</sub> = 10 V * <sup>1</sup>
Forward transfer admittance	y <sub>fs</sub>	6.0	10.0	—	S	I <sub>D</sub> = 8 A, V <sub>DS</sub> = 10 V * <sup>1</sup>
Input capacitance	C <sub>iss</sub>	—	1250	—	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0,
Output capacitance	C <sub>oss</sub>	—	510	—	pF	f = 1 MHz
Reverse transfer capacitance	C <sub>rss</sub>	—	85	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	24	—	ns	I <sub>D</sub> = 8 A, V <sub>GS</sub> = 10 V,
Rise time	t <sub>r</sub>	—	85	—	ns	R <sub>L</sub> = 3.75 Ω
Turn-off delay time	t <sub>d(off)</sub>	—	110	—	ns	
Fall time	t <sub>f</sub>	—	60	—	ns	
Body to drain diode forward voltage	V <sub>DF</sub>	—	1.0	—	V	I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery time	t <sub>r</sub>	—	400	—	ns	I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0, di <sub>F</sub> /dt = 100 A/µs

Note 1. Pulse test

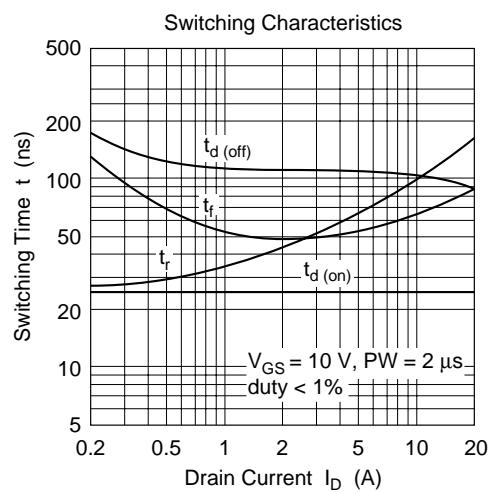
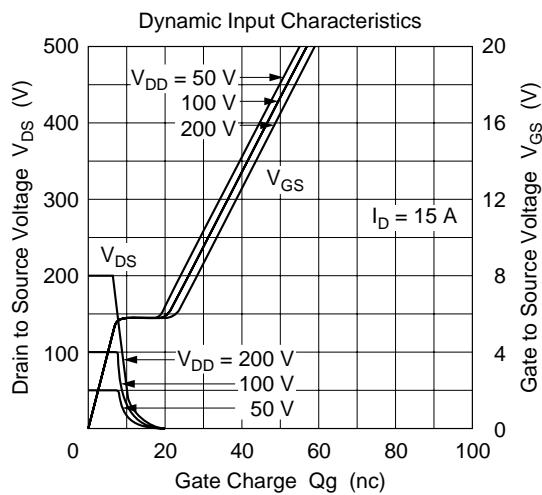
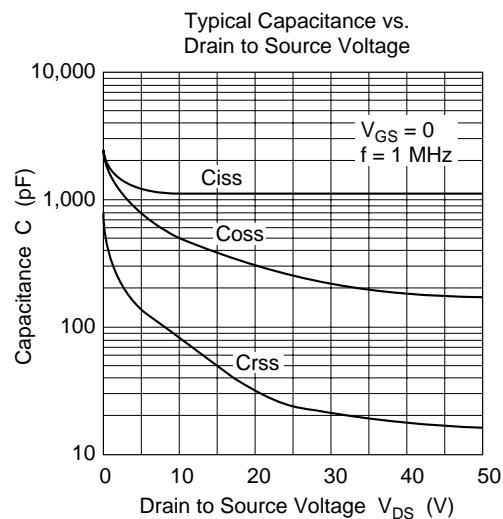
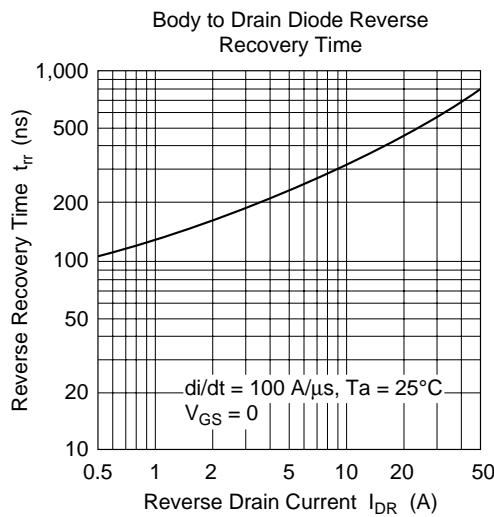
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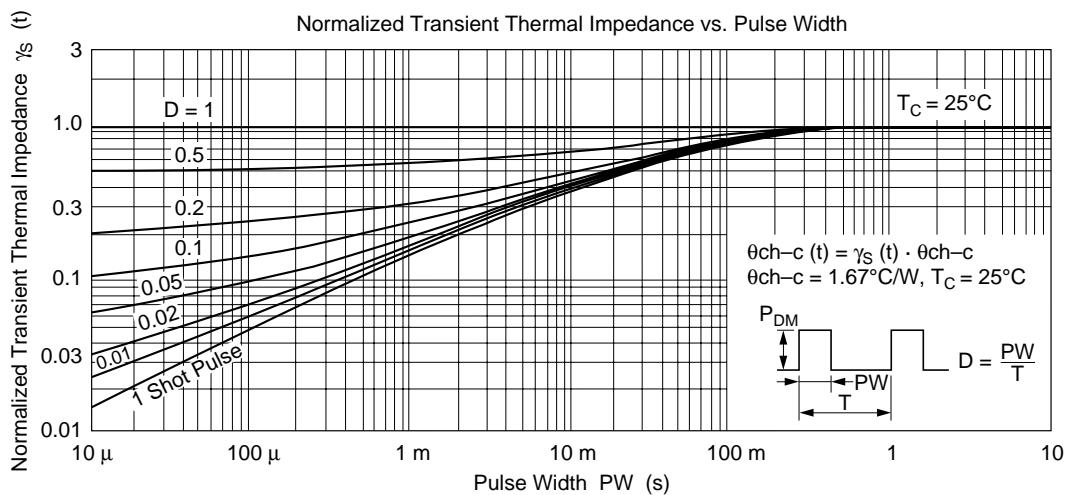
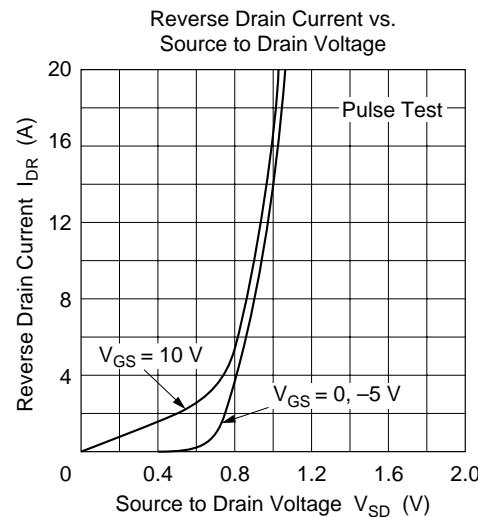


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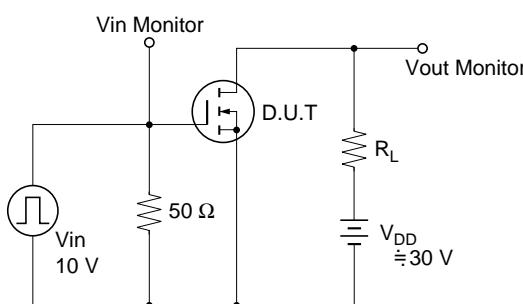


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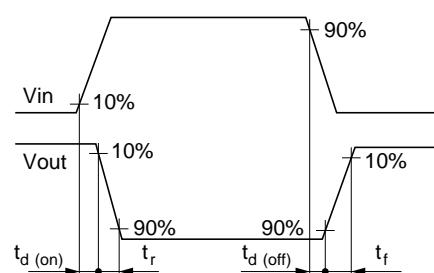




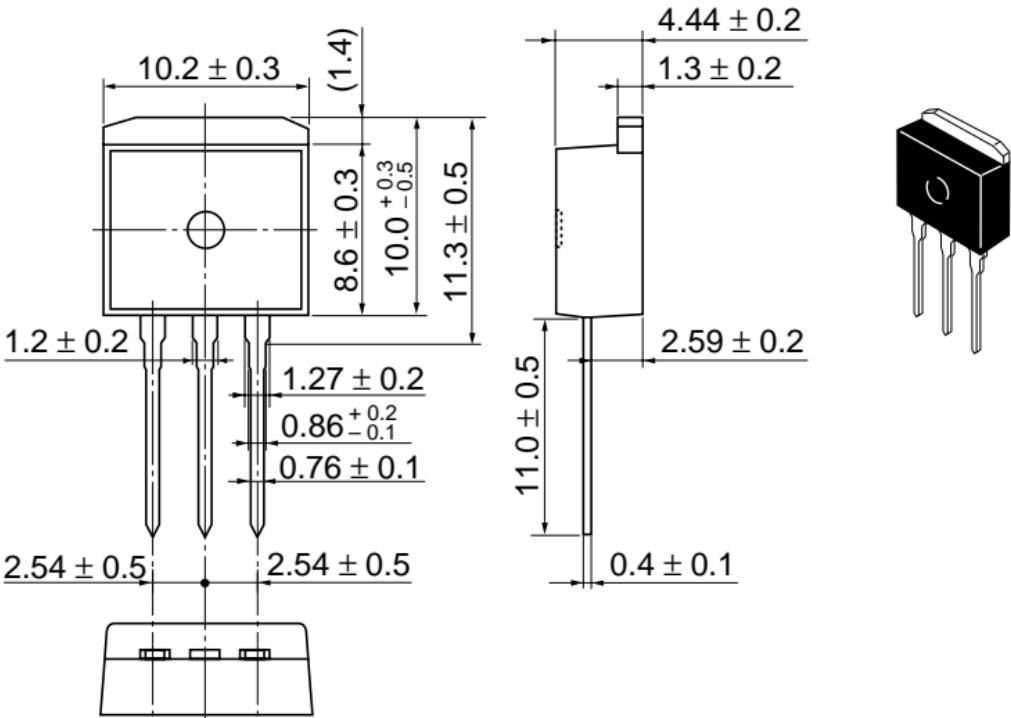
Switching Time Test Circuit



Waveforms



Unit: mm



Hitachi Code	LDPAK (L)
JEDEC	—
EIAJ	—
Weight (reference value)	1.4 g

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